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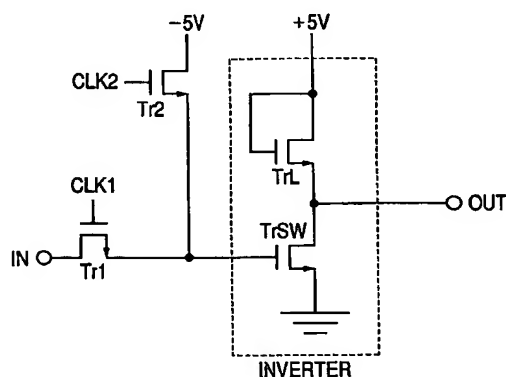
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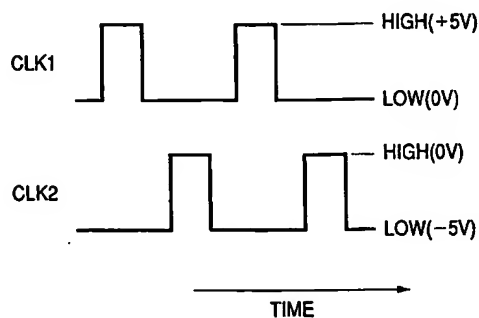
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(54) Title: DRIVING METHOD OF INTEGRATED CIRCUIT



(57) Abstract: A field-effect transistor (T2SW) in a semiconductor integrated circuit is driven by periodically applying positive and negative voltage pulses, with reference to the voltage applied to the source and drain electrodes, to the gate electrode. Stable operation of integrated circuit is realized by a simple method, even if the integrated circuit includes a field-effect transistor exhibiting a readily fluctuating threshold voltage.





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